WHAT IS CLAIMED IS:

1. An apparatus comprising:
a loading chamber;
a first chamber for forming a light-emitting film by a liquid jet method;
a second chamber for forming a conductive film by a sputtering method;
a third chamber for forming an insulating film by a sputtering method; and
an unloading chamber,
wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the first chamber to the third chamber and the unloading chamber.

2. An apparatus comprising:
a loading chamber;
a common chamber;
a first chamber for forming a light-emitting film by a liquid jet method;
a second chamber for forming a conductive film by a sputtering method;
a third chamber for forming an insulating film by a sputtering method; and
an unloading chamber,
wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the common chamber, the first chamber to the third chamber and the unloading chamber.

3. An apparatus comprising:
a loading chamber;
a first chamber for forming a light-emitting film by a printing method;
a second chamber for forming a conductive film by a sputtering method;
a third chamber for forming an insulating film by a sputtering method; and
an unloading chamber,
wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the first chamber to the third chamber and the unloading chamber.

4. An apparatus comprising:
a loading chamber;
a common chamber;
a first chamber for forming a light-emitting film by a printing method;
a second chamber for forming a conductive film by a sputtering method;
a third chamber for forming an insulating film by a sputtering method; and
an unloading chamber,
wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the common chamber, the first chamber to the third chamber and the unloading chamber.

5. An apparatus comprising:

a loading chamber;
a first chamber for forming a light-emitting film by a spray method;
a second chamber for forming a conductive film by a sputtering method;
a third chamber for forming an insulating film by a sputtering method; and
an unloading chamber,
wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the first chamber to the third chamber and the unloading chamber.

6. An apparatus comprising:
a loading chamber;
a common chamber;
a first chamber for forming a light-emitting film by a spray method;
a second chamber for forming a conductive film by a sputtering method;
a third chamber for forming an insulating film by a sputtering method; and
an unloading chamber,
wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the common chamber, the first chamber to the third chamber and the unloading chamber.

7. An apparatus according to any one of claims 1 to 6, wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

8. An apparatus according to any one of claims 1 to 6, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

9. An apparatus according to any one of claims 1 to 6, wherein the conductive film is an oxide conductive film.

10. An apparatus according to any one of claims 1 to 6, wherein the insulating film comprises silicon nitride.

11. An apparatus according to any one of claims 1 to 6, wherein the loading chamber and the unloading chamber are constituted as a unitary structure.

12. A method of producing a light-emitting device comprising the steps of:
forming a light-emitting film on an electrode by an ink jet method;
forming a conductive film on the light-emitting film by a sputtering method; and
forming an insulating film on the conductive film by a sputtering method,
wherein the light-emitting film forming step, the conductive film forming step and the insulating film forming step are carried out while holding a substrate having the

electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30° .

13. A method of producing a light-emitting device comprising the steps of:
forming a light-emitting film on an electrode by a printing method;
forming a film on the light-emitting film by a sputtering method; and
forming an insulating film on the conductive film by a sputtering method,
wherein the light-emitting film forming step, the conductive film forming step and the insulating film forming step are carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30° .

14. A method of producing a light-emitting device comprising the steps of:
forming a light-emitting film on an electrode by a spray method;
forming a conductive film on the light-emitting material by a sputtering method; and
forming an insulating film on the conductive film by a sputtering method,
wherein the light-emitting film forming step, the conductive film forming step and the insulating film forming step are carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30° .

15. A method of producing a light-emitting device according to any one of claims 12 to 14, wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

16. A method of producing a light-emitting device according to any one of claims 12 to 14, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

17. A method of producing a light-emitting device according to any one of claims 12 to 14, wherein the conductive film is an oxide conductor film.

18. A method of producing a light-emitting device according to any one of claims 12 to 14, wherein the insulating film comprises silicon nitride.